

STATIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
BV _{DSX}	Drain – Source Breakdown Voltage	V _{GS} = –10V I _D = 10mA	BUZ900DP	160			V
			BUZ901DP	200			
BV _{GSS}	Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100μA	±14			V
V _{GS(OFF)}	Gate – Source Cut-Off Voltage	V _{DS} = 10V	I _D = 100mA	0.1		1.5	V
V _{DS(SAT)} *	Drain – Source Saturation Voltage	V _{GD} = 0	I _D = 16A			12	V
I _{DSX}	Drain – Source Cut-Off Current	V _{GS} = –10V	V _{DS} = 160V BUZ900DP			10	mA
			V _{DS} = 200V BUZ901DP			10	
yfs*	Forward Transfer Admittance	V _{DS} = 10V	I _D = 3A	1.4		4	S

DYNAMIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic		Test Conditions		Min.	Typ.	Max.	Unit
C _{iss}	Input Capacitance	V _{DS} = 10V f = 1MHz			950		pF
C _{oss}	Output Capacitance				550		
C _{rss}	Reverse Transfer Capacitance				18		
t _{on}	Turn-on Time	V _{DS} = 20V I _D = 7A			160		ns
t _{off}	Turn-off Time				80		

* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.



